

[本期目录](#) | [下期目录](#) | [过刊浏览](#) | [高级检索](#)[\[打印本页\]](#) [\[关闭\]](#)**研究论文****掺硼对超纳米金刚石薄膜的影响**王玉乾¹; 王兵²; 孟祥钦²; 甘孔银²

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摘要:

采用微波等离子体化学气相沉积(MPCVD)技术,利用氩气、甲烷、二氧化碳混合气体,制备出平均晶粒尺寸在7.480 nm左右,表面粗糙度在15.72 nm左右的高质量的超纳米金刚石薄膜;在此工艺基础上以硼烷作为掺杂气体,合成掺硼的金刚石薄膜。表征结果显示在一定的浓度范围内随着硼烷气体的通入,金刚石薄膜的晶粒尺寸及表面粗糙度增大、结晶性变好,不再具有超纳米金刚石膜的显微结构和表面形态;同时膜材的物相组成也发生改变,金刚石组份逐渐增多,并且膜层内出现了更明显的应力以及更好的导电性能。

关键词: 无机非金属材料 掺硼 超纳米金刚石薄膜 化学气相沉积

Effect of B-doping on ultrananocrystalline diamond filmWANG Yuqian¹; WANG Bing²; MENG Xiangqin²; GAN Kongyin²

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Abstract:

High-quality ultrananocrystalline diamond film was prepared with Ar/CH₄/CO₂ by using microwave plasma chemical vapor deposition (MPCVD) technology. The average size of the crystalline grains and surface roughness are about 7.480 nm and 15.72 nm, respectively. B-doped diamond thin film was synthesized by adding B₂H₆ into the gas resource. The results showed that within a certain limits along with the addition of B₂H₆, the grains size and surfaces roughness of the diamond thin films increased dramatically, and their crystallinity got better. The diamond thin film no longer had the characteristics of the ultrananocrystalline diamond film. Meanwhile, with the addition of B₂H₆, the diamond phase constitutes in these films increased gradually, and more obvious residual stress and better conductivity appeared at the same time.

Keywords: inorganic non-metallic materials B-doping ultrananocrystalline diamond film CVD

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